



THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Hiroyuki ABE et al.

Application No.: 08/930,449

Filed: October 7, 1997

Docket No.: JAO 39514

For: HIGH ENERGY SUPPLY APPARATUS, METHOD OF FORMING
CRYSTALLINE FILM AND METHOD OF MANUFACTURING THIN
FILM ELECTRONIC DEVICE

SUPPLEMENTAL PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Prior to initial examination, please amend the above-
identified application as follows.

IN THE SPECIFICATION:

A Substitute Specification was filed on
September 30, 1997. Please amend the Substitute Specification
as follows:

Page 1, line 37, change " $10 \text{ cm}^{-2} \cdot \text{V}^{-1} \cdot \text{S}^{-1}$ " to $100 \text{ cm}^{-2} \cdot \text{V}^{-1} \cdot \text{S}^{-1}$ " to $--10 \text{ cm}^2 \cdot \text{V}^{-1} \cdot \text{S}^{-1}$ to $100 \text{ cm}^2 \cdot \text{V}^{-1} \cdot \text{S}^{-1}--$.

Page 2, line 5-6, change " $0.1 \text{ cm}^{-2} \cdot \text{V}^{-1} \cdot \text{S}^{-1}$ " to $1 \text{ cm}^{-2} \cdot \text{V}^{-1} \cdot \text{S}^{-1}$ " to $--0.1 \text{ cm}^2 \cdot \text{V}^{-1} \cdot \text{S}^{-1}$ to $1 \text{ cm}^2 \cdot \text{V}^{-1} \cdot \text{S}^{-1}--$.

Page 12, line 12, change " $F = \frac{1}{6} CV = \frac{1}{\sqrt{3kTm}}$ " to

B, $F = \frac{1}{6} cv = \frac{1}{2 \sqrt{3kTm}}$